ABSTRACT

A photoresist base material comprising an extreme ultra-violet reactive organic compound of the following formula (1),

wherein A is a central structure that is an 10 aliphatic group having 1 to 50 carbon atoms, an aromatic group having 6 to 50 carbon atoms, an organic group containing these together or an organic group having a cyclic structure formed by repetition of these, each of B to D is an extreme ultra-violet reactive group, a group having reactivity to the action of a chromophore active to extreme ultra-violet, or a C_1 to C_{50} aliphatic group, C_6 to C_{50} aromatic group, an organic group containing these together or a substituent having a branched structure, containing such a reactive group, X to Z are single bonds or ether bonds, 1 to n are integers of 0 to 5 satisfying 1 + m + n \geq 1, and A to D may contain a substituent having a heteroatom. The photoresist base material and a composition thereof enable ultrafine processing based on extreme ultraviolet.